

**COPPER BONDING WIRE FOR SEMICONDUCTOR DEVICES AND
SEMICONDUCTOR DEVICE**

ABSTRACT

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There is provided a copper bonding wire having an improved storage life in the atmosphere. There is specifically provided a copper bonding wire for semiconductor devices characterized in that a density of
10 crystal grain boundary on a surface of the wire is 0.6 ($\mu\text{m}/\mu\text{m}^2$) or more and 1.6 ($\mu\text{m}/\mu\text{m}^2$) or less.

[No figure]